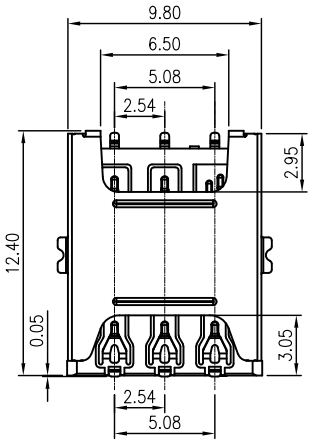
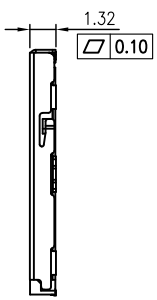
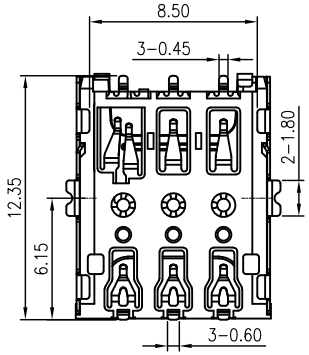
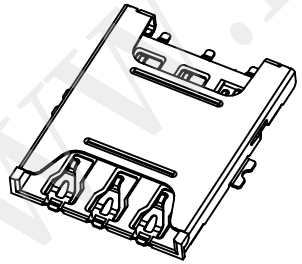
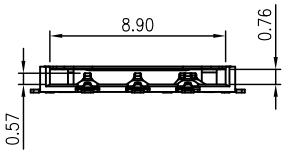
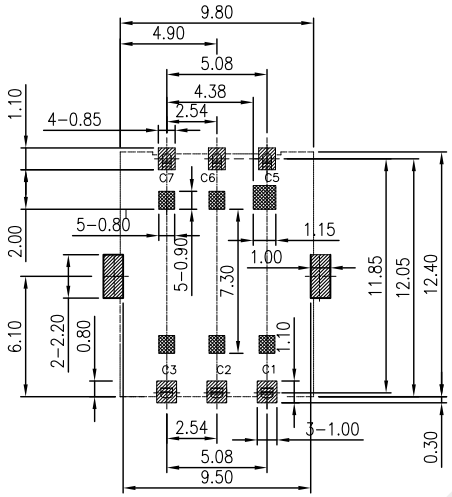










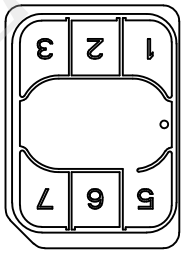


RECOMMENDED P.C.B LAYOUTCOMPONENT SIDE(TOLERANCE ±0.05)

PAD AREA
CONNECTOR DUTLINEND
PATTERN
ANDIAHOLEIN THIS AREA

Nano SIM Circuit Description:

PIN No.	FUNCTION
C1	VCC
C2	RST
C3	CLK
C5	GND
C6	VPP
C7	I/O



TECHNICAL CHARACTERISTICS1.
1.General Characteristics
Dimensions:12.40LX9.80WX1.35H mm
Weight: Approx 0.50±0.2g
Durability:1,500cycles min.
2.Electrical Characteristics
Contact resistance:50mΩ typical,
100m. max
Insulation resistance:>1000MΩ/500V DC
Solderability
Vaporphase:215℃,30sec.MaxIR
reflow:250C,5sec.MaxManual soldering:370°C,3sec.Max
4.Environmental Characteristics
Operating temperature:-40°C~+85°C
Operating humidity:10%~+95%RH

NO.	DESCRIPTION	Q'TY	Material	Finish
3	CONTACT	1	COPPER ALLOY	CONTACT AREA:GOLD PLATED
2	SHELL	1	STAINLESS STEEL	
1	HOUSING	1	LCP UL94V-0	COLOR:BLACK

深圳市华宇创精密电子有限公司

TOLERANCE: X.X ±0.30, X.XX ±0.25, X.XXX ±0.15, X.° ±2°, X.X° ±0.5°	DRAWED BY: 陈一鸣	DATE: 2014-02-23	PART NAME: NANO SIM 6P 1.32H 脚向外
	CHECKED BY: 马跃	DATE: 2014-02-23	PART NO.: HYC385-SIM06-132
UNIT: mm [inch]	APPROVED BY: 邱敏	DATE: 2014-02-23	MOLD NO.:
SCALE:1:1 SIZE: A4			DRAW NO.: HYC-2602281041
			SHEET NO.: 1 OF 1